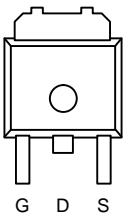




N-Channel 22-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^d
24 ^C	0.006 @ $V_{GS} = 10$ V	80
	0.0095 @ $V_{GS} = 4.5$ V	64

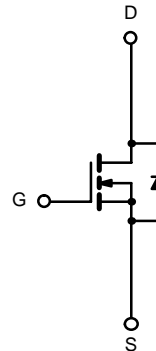
TO-252



Top View

Order Number:
SUD50N024-06P

Drain Connected to Tab



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- PWM Optimized for High Efficiency

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 - Desktop
 - Server

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit	
Drain-Source Pulse Voltage	$V_{DS(pulse)}$	24 ^C	V	
Drain-Source Voltage	V_{DS}	22		
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ^a	I_D	$T_C = 25^\circ\text{C}$	80 ^d	A
		$T_C = 100^\circ\text{C}$	56 ^d	
Pulsed Drain Current	I_{DM}	100		
Continuous Source Current (Diode Conduction) ^a	I_S	26		
Avalanche Current, Single Pulse	I_{AS}	45		
Avalanche Energy, Single Pulse	E_{AS}	101	mJ	
Maximum Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	6.8 ^a	W
		$T_C = 25^\circ\text{C}$	65	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	18	$^\circ\text{C}/\text{W}$
		Steady State	40	
Maximum Junction-to-Case	R_{thJC}	1.9	2.3	

Notes

- Surface Mounted on FR4 Board, $t \leq 10$ sec.
- Limited by package
- Pulse condition: $T_A = 105^\circ\text{C}$, 50 ns, 300 kHz operation
- Calculation based on maximum allowable Junction Temperature. Package limitation current is 50 A.



Vishay Siliconix

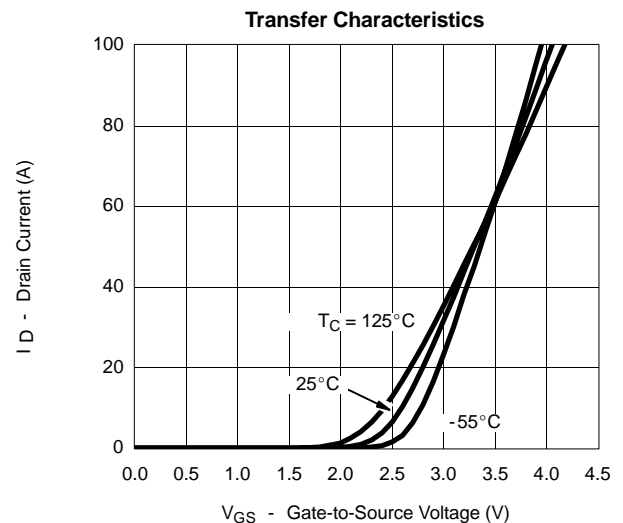
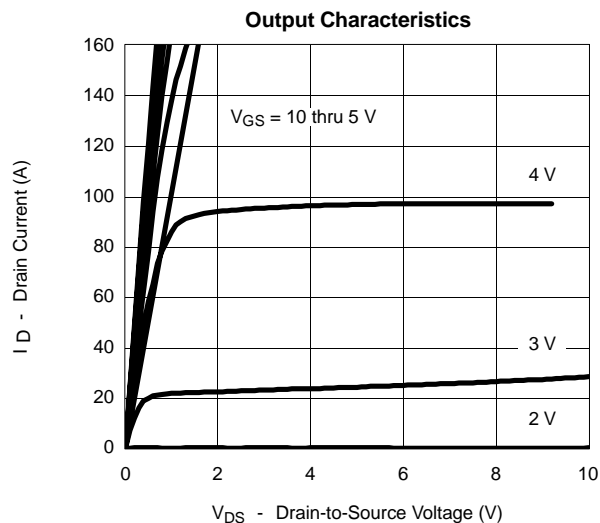
New Product

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	22			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.8		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1	μA
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 125 °C			50	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0046	0.006	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0084	
Forward Transconductance ^b	g _{fs}	V _{GS} = 4.5 V, I _D = 20 A		0.0073	0.0095	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	15			S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 MHz		2550		pF
Output Capacitance	C _{oss}			900		
Reverse Transfer Capacitance	C _{rss}			415		
Gate Resistance	R _G			1.5		Ω
Total Gate Charge ^c	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 50 A		19	30	nC
Gate-Source Charge ^c	Q _{gs}			7.5		
Gate-Drain Charge ^c	Q _{gd}			6.0		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 10 V, R _L = 0.2 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _G = 2.5 Ω		11	20	ns
Rise Time ^c	t _r			10	15	
Turn-Off Delay Time ^c	t _{d(off)}			24	35	
Fall Time ^c	t _f			9	15	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I _{SM}				100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		35	70	ns

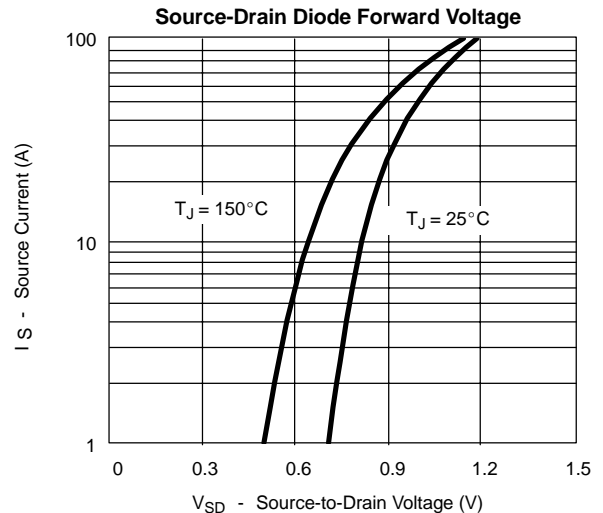
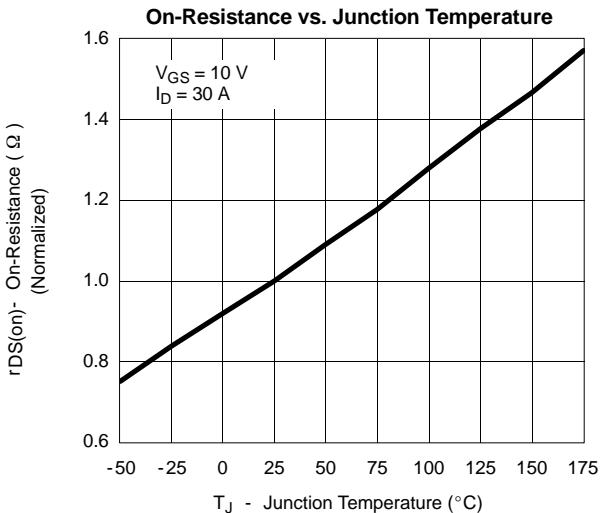
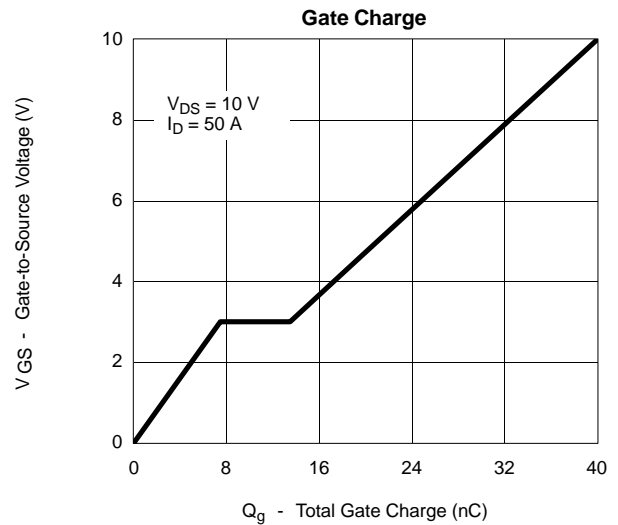
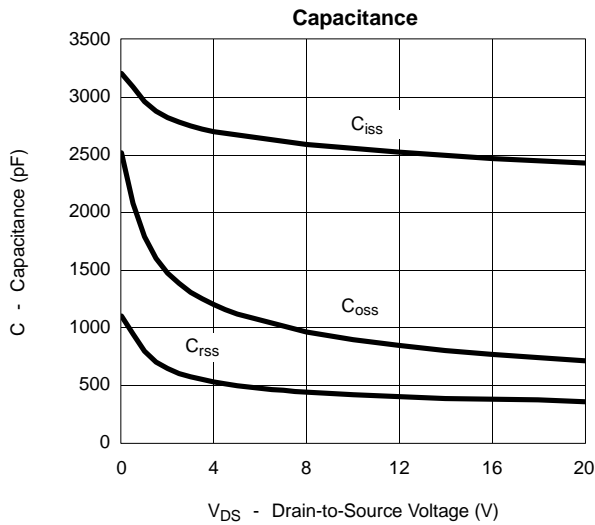
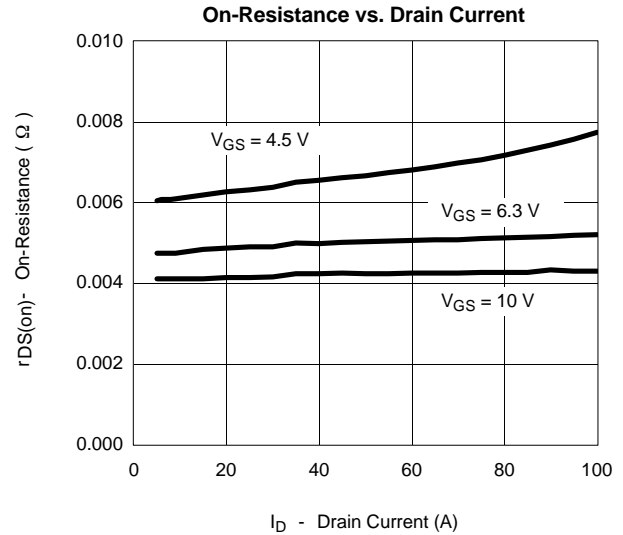
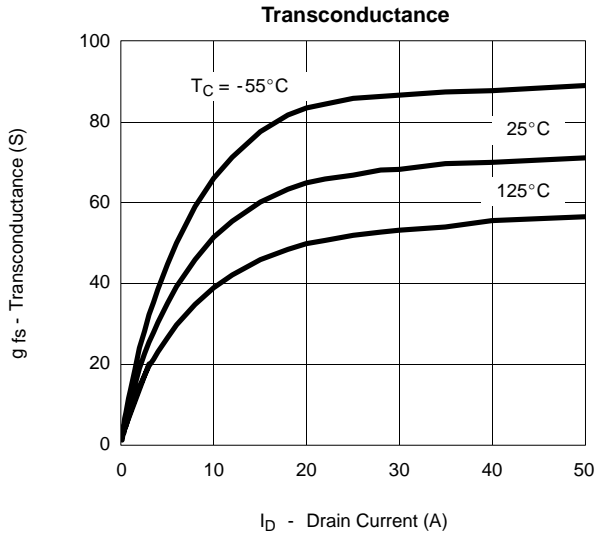
Notes

- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



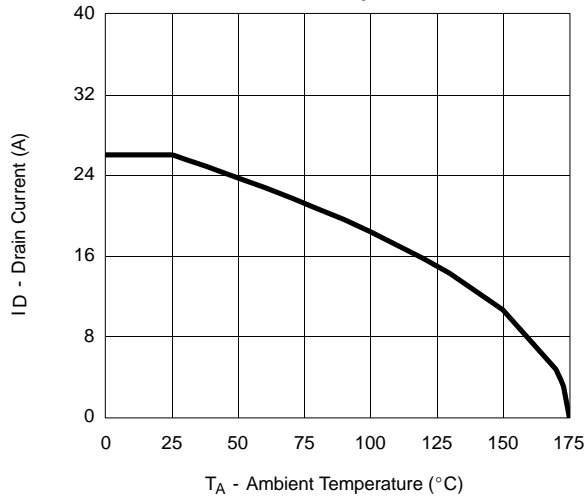
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



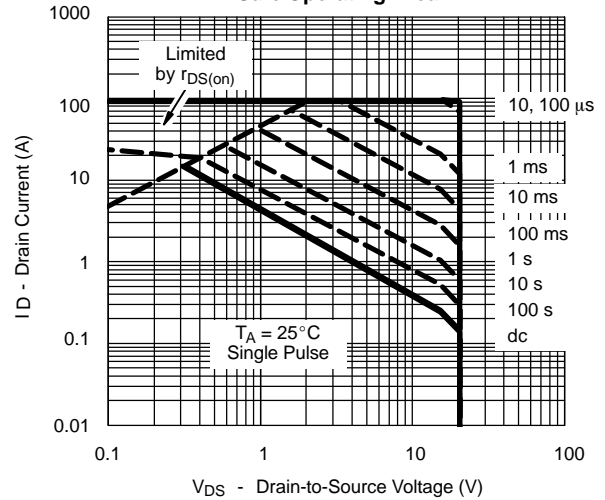


THERMAL RATINGS

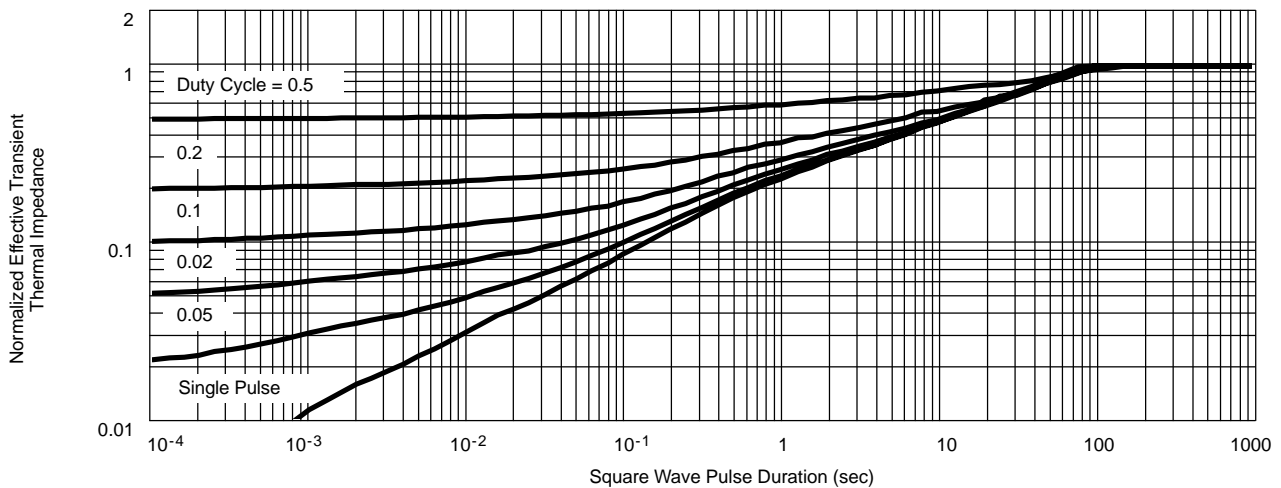
Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

